

Wideband, Fast Settling, Unity Gain Stable, Video Operational Amplifier

July 1994

Features

- This Circuit is Processed in Accordance to MIL-STD-883 and is Fully Conformant Under the Provisions of Paragraph 1.2.1
- Low AC Variability Over Process and Temperature
- Low Supply Current. 11mA (Max)
- Unity Gain Bandwidth 50MHz (Typ)
- High Slew Rate. 290V/ μ s (Typ)
- Low Offset Voltage. 1mV (Typ)
- Full Power Bandwidth 4.6MHz (Typ)
- Low Differential Gain/Phase 0.03%/0.03° (Typ)

Applications

- Pulse and Video Amplifiers
- Wideband Amplifiers
- Fast Sample and Hold Circuits
- Fast, Precise D/A Converters
- High Speed A/D Input Buffer

Description

The HA-2841/883 is a wideband, unity gain stable, operational amplifier featuring a 50MHz unity gain bandwidth, and excellent DC specifications. This amplifier's performance is further enhanced through stable operation down to closed loop gains of +1, the inclusion of offset null controls, and by its excellent video performance.

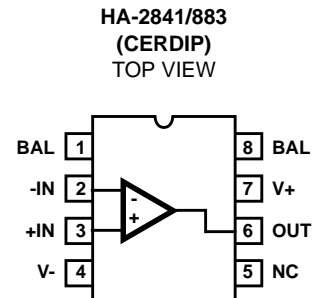
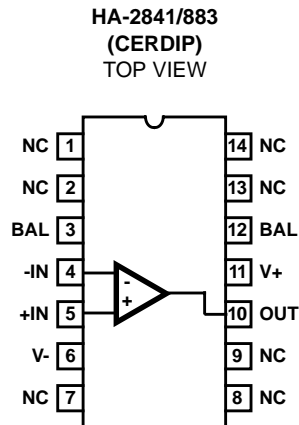
The capabilities of the HA-2841/883 are ideally suited for high speed pulse and video amplifier circuits, where high slew rates and wide bandwidth are required. Gain flatness of 0.05dB, combined with differential gain and phase specifications of 0.03%, and 0.03 degrees, respectively, make the HA-2841/883 ideal for component and composite video applications.

A zener/nichrome based reference circuit, coupled with advanced laser trimming techniques, yields a supply current with a low temperature coefficient and low lot-to-lot variability. Tighter I_{CC} control translates to more consistent AC parameters ensuring that units from each lot perform the same way, and easing the task of designing systems for wide temperature ranges.

Ordering Information

| PART NUMBER | TEMPERATURE RANGE | PACKAGE |
|--------------|-------------------|----------------|
| HA1-2841/883 | -55°C to +125°C | 14 Lead CerDIP |
| HA7-2841/883 | -55°C to +125°C | 8 Lead CerDIP |

Pinouts



NOTE: (NC) No Connection pins may be tied to a ground plane for better isolation and heat dissipation.

Specifications HA-2841/883

Absolute Maximum Ratings

| | |
|---|-----------------|
| Voltage between V+ and V- Terminals | +35V |
| Differential Input Voltage | 6V |
| Voltage at Either Input Terminal | V+ to V- |
| Peak Output Current ($\leq 10\%$ Duty Cycle) | 50mA |
| Junction Temperature (T_J) | +175°C |
| Storage Temperature Range | -65°C to +150°C |
| ESD Rating | <2000V |
| Lead Temperature (Soldering 10s) | +300°C |

Thermal Information

| | | |
|--|---------------|---------------|
| Thermal Resistance | θ_{JA} | θ_{JC} |
| 14 Pin CerDIP Package | 73°C/W | 18°C/W |
| 8 Pin CerDIP Package | 110°C/W | 27°C/W |
| Package Power Dissipation Limit at +75°C for $T_J \leq +175^\circ\text{C}$ | | |
| 14 Pin CerDIP Package | 1.05W | |
| 8 Pin CerDIP Package | 0.9W | |
| Package Power Dissipation Derating Factor Above +75°C | | |
| 14 Pin CerDIP Package | 10.5mW/°C | |
| 8 Pin CerDIP Package | 9mW/°C | |

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Operating Conditions

| | | |
|---------------------------------------|--------------------------------------|------------------------------|
| Operating Temperature Range | -55°C to +125°C | $V_{INCM} \leq 1/2(V+ - V-)$ |
| Operating Supply Voltage | $\pm 12\text{V}$ to $\pm 15\text{V}$ | $R_L \geq 1\text{k}\Omega$ |

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS

Device Tested at: $V_{SUPPLY} = \pm 15\text{V}$, $R_{SOURCE} = 100\Omega$, $R_{LOAD} = 100\text{k}\Omega$, $V_{OUT} = 0\text{V}$, Unless Otherwise Specified.

| PARAMETERS | SYMBOL | CONDITIONS | GROUP A SUBGROUP | TEMPERATURE | LIMITS | | UNITS |
|-----------------------------|-------------|--|------------------|---------------|--------|-----|---------------|
| | | | | | MIN | MAX | |
| Input Offset Voltage | V_{IO} | $V_{CM} = 0\text{V}$ | 1 | +25°C | -4 | 4 | mV |
| | | | 2, 3 | +125°C, -55°C | -8 | 8 | mV |
| Input Bias Current | + I_B | $V_{CM} = 0\text{V}$, + $R_S = 1.1\text{k}\Omega$ - $R_S = 100\Omega$ | 1 | +25°C | -10 | 10 | μA |
| | | | 2, 3 | +125°C, -55°C | -20 | 20 | μA |
| | - I_B | $V_{CM} = 0\text{V}$, + $R_S = 100\Omega$ - $R_S = 1.1\text{k}\Omega$ | 1 | +25°C | -10 | 10 | μA |
| | | | 2, 3 | +125°C, -55°C | -20 | 20 | μA |
| Input Offset Current | I_{IO} | $V_{CM} = 0\text{V}$, + $R_S = 1.1\text{k}\Omega$ - $R_S = 1.1\text{k}\Omega$ | 1 | +25°C | -1 | 1 | μA |
| | | | 2, 3 | +125°C, -55°C | -2 | 2 | μA |
| Common Mode Range | +CMR | $V+ = 5\text{V}$ $V- = -25\text{V}$ | 1 | +25°C | 10 | - | V |
| | | | 2, 3 | +125°C, -55°C | 10 | - | V |
| | -CMR | $V+ = 25\text{V}$ $V- = -5\text{V}$ | 1 | +25°C | - | -10 | V |
| | | | 2, 3 | +125°C, -55°C | - | -10 | V |
| Large Signal Voltage Gain | + A_{VOL} | $V_{OUT} = 0\text{V}$ and +10V $R_L = 1\text{k}\Omega$ | 4 | +25°C | 10 | - | kV/V |
| | | | 5, 6 | +125°C, -55°C | 5 | - | kV/V |
| | - A_{VOL} | $V_{OUT} = 0\text{V}$ and -10V $R_L = 1\text{k}\Omega$ | 4 | +25°C | 10 | - | kV/V |
| | | | 5, 6 | +125°C, -55°C | 5 | - | kV/V |
| Common Mode Rejection Ratio | +CMRR | $\Delta V_{CM} = 10\text{V}$, $V_{OUT} = -10\text{V}$ $V+ = 5\text{V}$, $V- = -25\text{V}$ | 1 | +25°C | 86 | - | dB |
| | | | 2, 3 | +125°C, -55°C | 80 | - | dB |
| | -CMRR | $\Delta V_{CM} = -10\text{V}$, $V_{OUT} = 10\text{V}$ $V+ = 25\text{V}$, $V- = -5\text{V}$ | 1 | +25°C | 86 | - | dB |
| | | | 2, 3 | +125°C, -55°C | 80 | - | dB |

Specifications HA-2841/883

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)

Device Tested at: $V_{SUPPLY} = \pm 15V$, $R_{SOURCE} = 100\Omega$, $R_{LOAD} = 100k\Omega$, $V_{OUT} = 0V$, Unless Otherwise Specified.

| PARAMETERS | SYMBOL | CONDITIONS | GROUP A SUBGROUP | TEMPERATURE | LIMITS | | UNITS |
|-----------------------------------|---------------------|---|---------------------|---------------|-------------------|-----|-------|
| | | | | | MIN | MAX | |
| Output Voltage Swing | +V _{OUT} | R _L = 1kΩ | 1 | +25°C | 10 | - | V |
| | | | 2, 3 | +125°C, -55°C | 10 | - | V |
| | -V _{OUT} | R _L = 1kΩ | 1 | +25°C | - | -10 | V |
| | | | 2, 3 | +125°C, -55°C | - | -10 | V |
| Output Current | +I _{OUT} | V _{OUT} = -5V, (Note 1) | 1 | +25°C | 25 | - | mA |
| | | | 2, 3 | +125°C, -55°C | 15 | - | mA |
| | -I _{OUT} | V _{OUT} = 5V, (Note 1) | 1 | +25°C | - | -25 | mA |
| | | | 2, 3 | +125°C, -55°C | - | -15 | mA |
| Quiescent Power Supply Current | +I _{CC} | V _{OUT} = 0V I _{OUT} = 0mA | 1 | +25°C | - | 11 | mA |
| | | | 2, 3 | +125°C, -55°C | - | 11 | mA |
| | -I _{CC} | V _{OUT} = 0V I _{OUT} = 0mA | 1 | +25°C | -11 | - | mA |
| | | | 2, 3 | +125°C, -55°C | -11 | - | mA |
| Power Supply Rejection Ratio | +PSRR | $\Delta V_{SUPPLY} = 10V$ V+ = 10V, V- = -15V V+ = 20V, V- = -15V | 1 | +25°C | 70 | - | dB |
| | | | 2, 3 | +125°C, -55°C | 70 | - | dB |
| | -PSRR | $\Delta V_{SUPPLY} = 10V$ V+ = 15V, V- = -10V V+ = 15V, V- = -20V | 1 | +25°C | 70 | - | dB |
| | | | 2, 3 | +125°C, -55°C | 70 | - | dB |
| Offset Voltage Adjustment | +V _{IOAdj} | (Note 2) | 1 | +25°C | V _{IO-1} | - | mV |
| | -V _{IOAdj} | (Note 2) | 1 | +25°C | V _{IO+1} | - | mV |

NOTES:

1. The output metal is sized to handle I_{OUT} = 10mA at a 50% duty cycle, for T_J = +175°C. For I_{OUT} = 15mA and T_J = +175°C, a duty cycle ≤33% is required.
2. Offset Adjustment range is |V_{IO} (measured) ±1mV| minimum referred to output. This test is for functionality only, to assure adjustment through 0V.

TABLE 2. AC ELECTRICAL PERFORMANCE CHARACTERISTICS

Table 2 Intentionally Left Blank. See A.C. Specifications in Table 3

Specifications HA-2841/883

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS

Device Characterized at: $V_{SUPPLY} = \pm 15V$, $R_{SOURCE} = 50\Omega$, $R_{LOAD} = 1k\Omega$, $V_{OUT} = 0V$, $A_V = +1V/V$, Unless Otherwise Specified.

| PARAMETERS | SYMBOL | CONDITIONS | NOTES | TEMPERATURE | LIMITS | | UNITS |
|-------------------------------|-----------|--|-------|-----------------|--------|-----|-------|
| | | | | | MIN | MAX | |
| Gain Bandwidth Product | GBWP | $V_O = 200mV$, $f_O = 0.1MHz$ | 1 | +25°C | 42 | - | MHz |
| | | $V_O = 200mV$, $f_O = 10MHz$ | 1 | +25°C | 44 | - | MHz |
| Slew Rate | SR | $V_O = -3V$ to +3V | 1, 3 | +25°C | 200 | - | V/μs |
| | SR | $V_O = -3V$ to +3V | 1, 3 | -55°C to +125°C | 187 | - | V/μs |
| Rise Time | T_R | $V_O = 0V$ to +200mV $C_L < 10pF$ | 1, 3 | +25°C | - | 6 | ns |
| | | | 1, 3 | -55°C to +125°C | - | 6 | ns |
| Fall Time | T_F | $V_O = 0V$ to -200mV $C_L < 10pF$ | 1, 3 | +25°C | - | 5 | ns |
| | | | 1, 3 | -55°C to +125°C | - | 6 | ns |
| Full Power Bandwidth | FPBW | $V_{PEAK} = +10V$ | 1, 2 | +25°C | 3.1 | - | MHz |
| | | | 1, 2 | -55°C to +125°C | 3.0 | - | MHz |
| Overshoot | +OS | $V_O = 0V$ to +200mV | 1 | +25°C | - | 60 | % |
| | | | 1 | -55°C to +125°C | - | 65 | % |
| | -OS | $V_O = 0V$ to -200mV | 1 | +25°C | - | 60 | % |
| | | | 1 | -55°C to +125°C | - | 70 | % |
| Closed Loop Output Resistance | R_{OUT} | $A_V > +1$ $V_M = 10V$, $\Delta I = 9mA$ | 1 | +25°C | - | 1 | Ω |

NOTES:

- Parameters listed in Table 3 are controlled via design or process parameters and are not directly tested at final production. These parameters are lab characterized upon initial design release, or upon design changes. These parameters are guaranteed by characterization based upon data from multiple production runs which reflect lot to lot and within lot variations.
- Full Power Bandwidth guarantee based on Slew Rate measurement using $FPBW = \text{Slew Rate} / (2\pi V_{PEAK})$.
- Measured between 10% and 90% points.

TABLE 4. ELECTRICAL TEST REQUIREMENTS

| MIL-STD-883 TEST REQUIREMENTS | SUBGROUPS (SEE TABLE 1) |
|---|---------------------------|
| Interim Electrical Parameters (Pre Burn-In) | 1 |
| Final Electrical Test Parameters | 1 (Note 1), 2, 3, 4, 5, 6 |
| Group A Test Requirements | 1, 2, 3, 4, 5, 6 |
| Groups C & D Endpoints | 1 |

NOTE:

- PDA applies to Subgroup 1 only.

Die Characteristics

DIE DIMENSIONS:

77 x 81 x 19 mils ± 1 mils
 1960 x 2060 x 483µm ± 25.4µm

METALLIZATION:

Type: Al, 1% Cu
 Thickness: 16kÅ ± 2kÅ

GLASSIVATION:

Type: Nitride over Silox
 Silox Thickness: 12kÅ ± 2kÅ
 Nitride thickness: 3.5kÅ ± 1kÅ

WORST CASE CURRENT DENSITY:

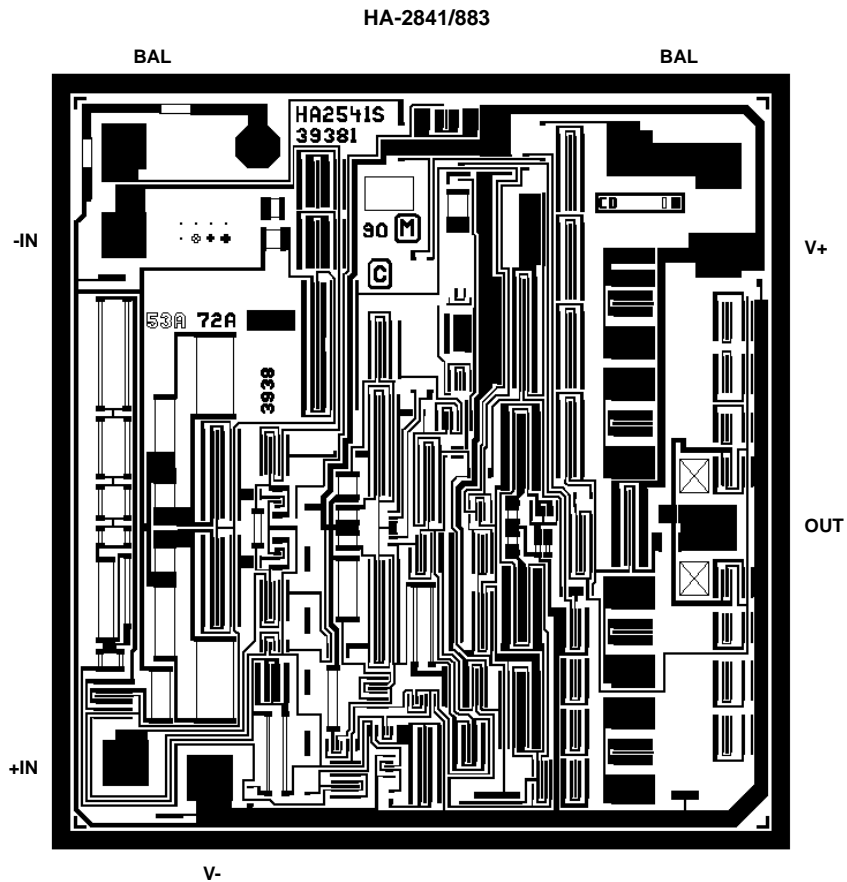
1.2 x 10⁵ A/cm² at 9.7mA

SUBSTRATE POTENTIAL (Powered Up): V-

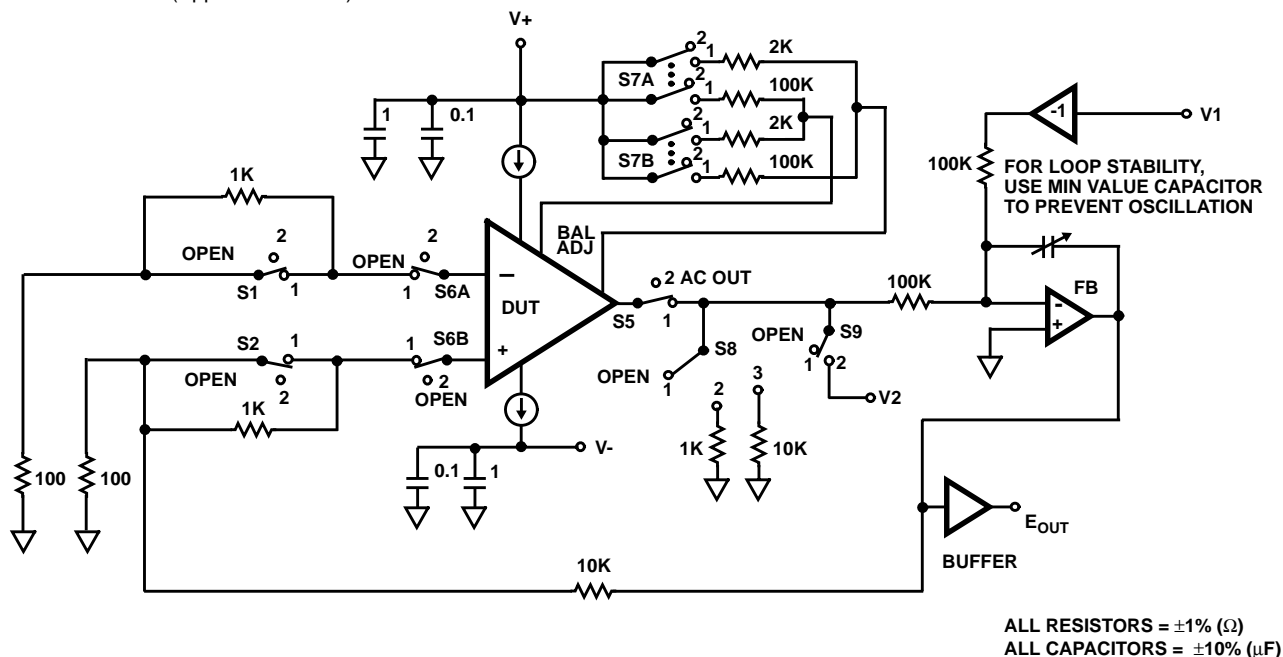
TRANSISTOR COUNT: 43

PROCESS: Bipolar Dielectric Isolation

Metallization Mask Layout

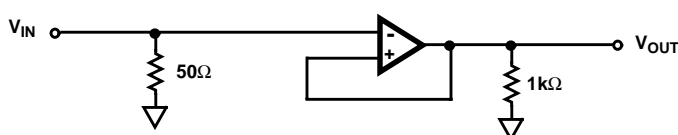


Test Circuit (Applies to Table 1)



Test Waveforms

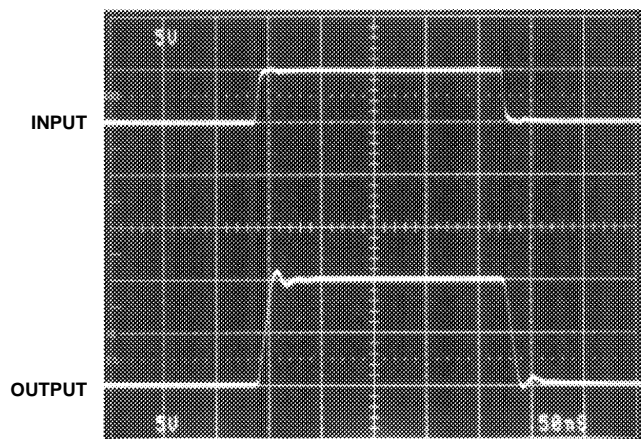
SIMPLIFIED TEST CIRCUIT FOR LARGE AND SMALL SIGNAL RESPONSE (Applies to Table 3)



$V_S = \pm 15\text{V}$
 $A_V = +1$
 $C_L \leq 10\text{pF}$
 NOTE: No Capacitive Load,
 Maintain Parasitics
 Less Than 10pF.

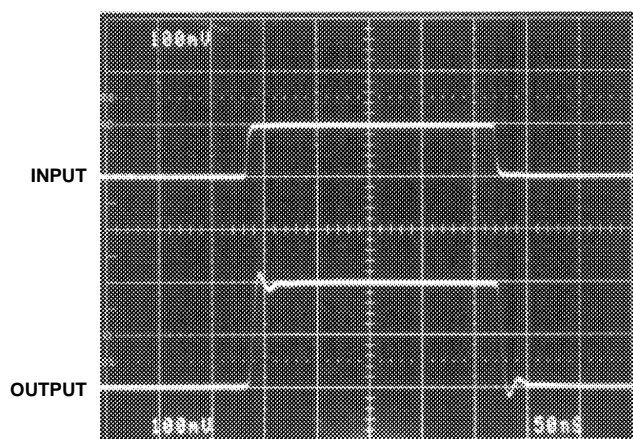
MEASURED LARGE SIGNAL RESPONSE

Vertical Scale: Input = 5V/Div., Output = 5V/Div.
 Horizontal Scale: 50ns/Div.



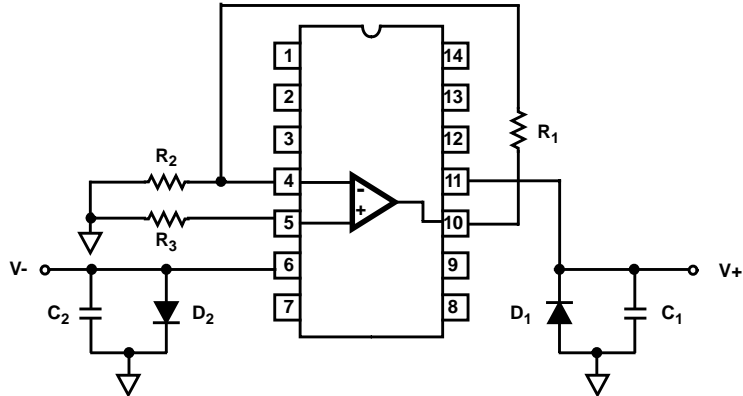
MEASURED SMALL SIGNAL RESPONSE

Vertical Scale: Input = 100mV/Div., Output = 100mV/Div.
 Horizontal Scale: 50ns/Div.

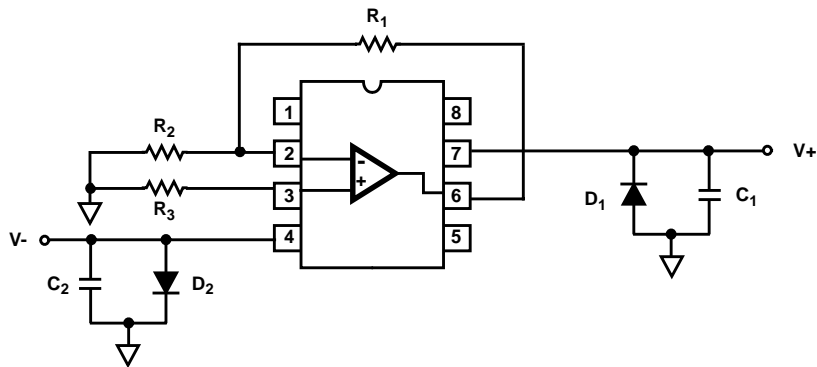


Burn-In Circuits

HA1-2841/883 CERAMIC DIP



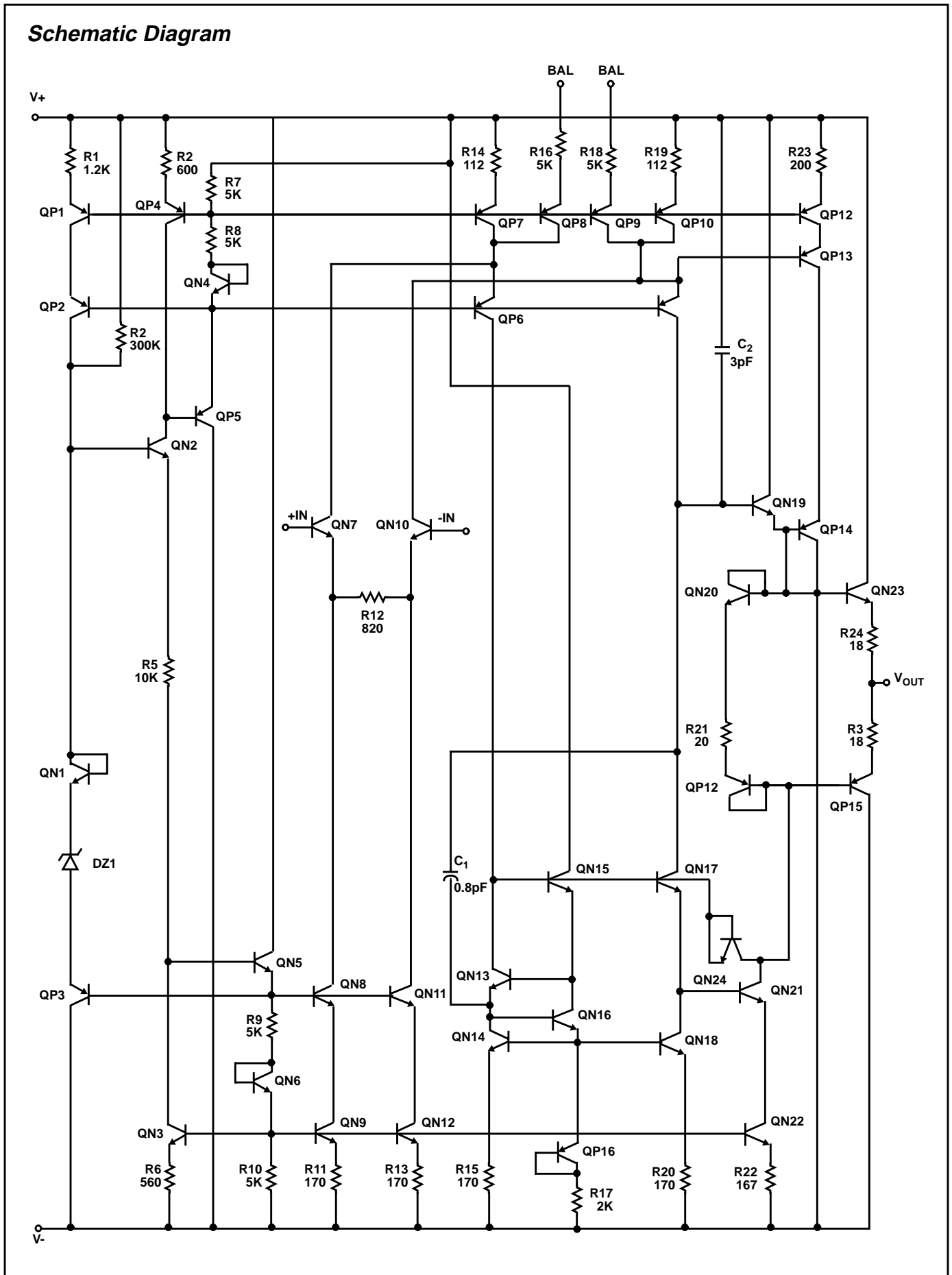
HA7-2841/883 CERAMIC DIP



NOTES:

1. $R_1 = 1M\Omega, \pm 5\%, 1/4W$ (Min)
2. $R_2 = 100k\Omega, \pm 5\%, 1/4W$ (Min), $= R_3$
3. $C_1 = C_2 = 0.01\mu F/\text{Socket}$ (Min) or $0.1\mu F/\text{Row}$, (Min)
4. $D_1 = D_2 = 1N4002$ or Equivalent/Board
5. $|V_+ - V_-| = 31V \pm 1V$

Schematic Diagram

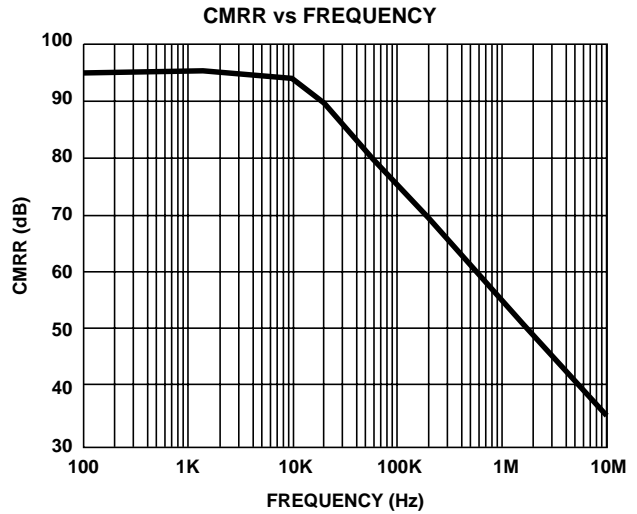
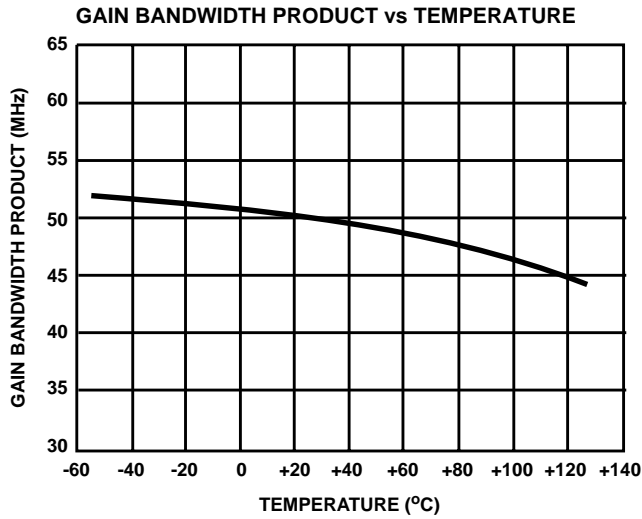
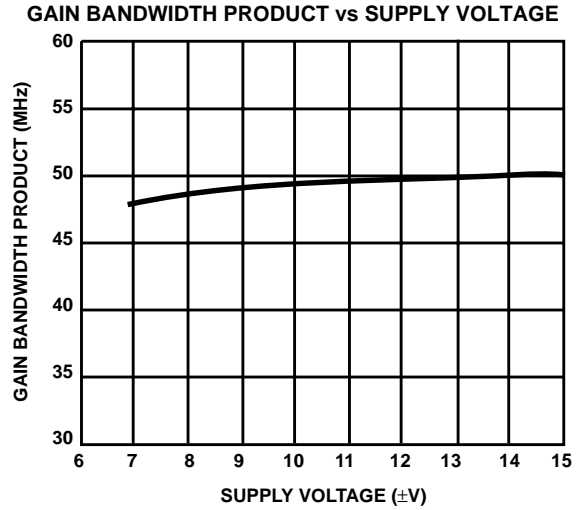
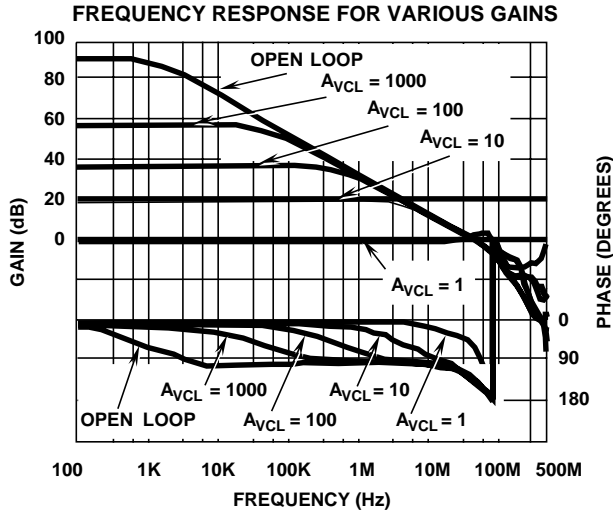


DESIGN INFORMATION

Wideband, Fast Settling, Unity Gain Stable, Video Operational Amplifier

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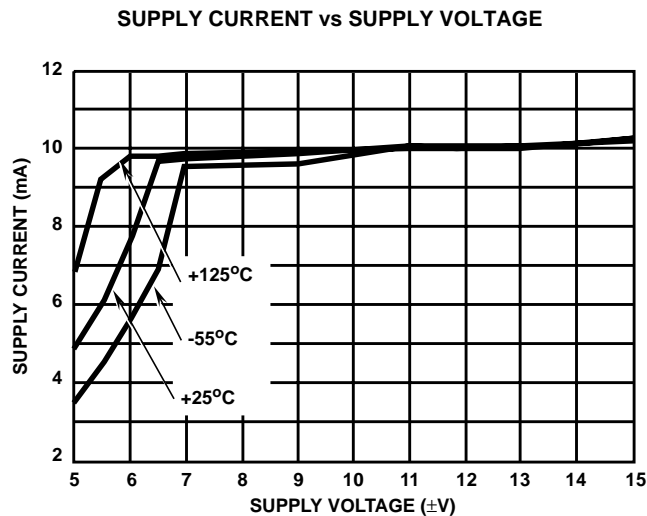
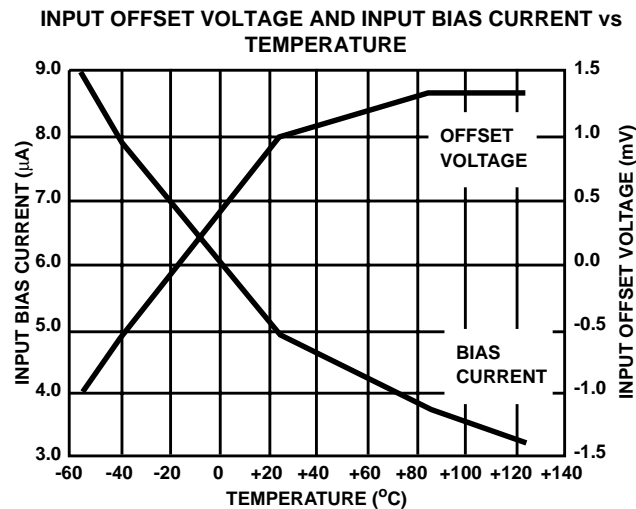
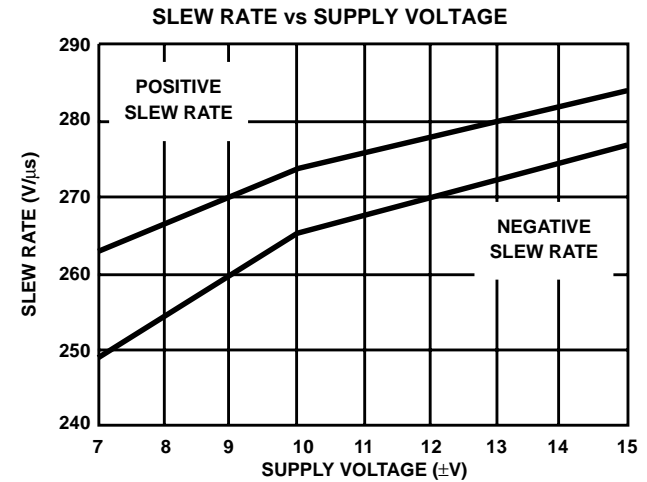
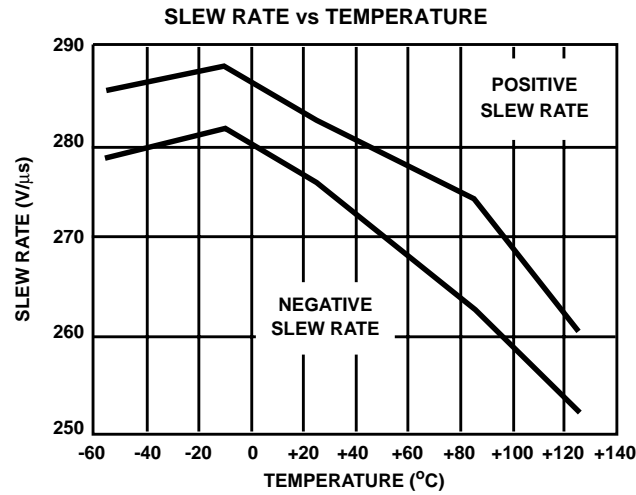
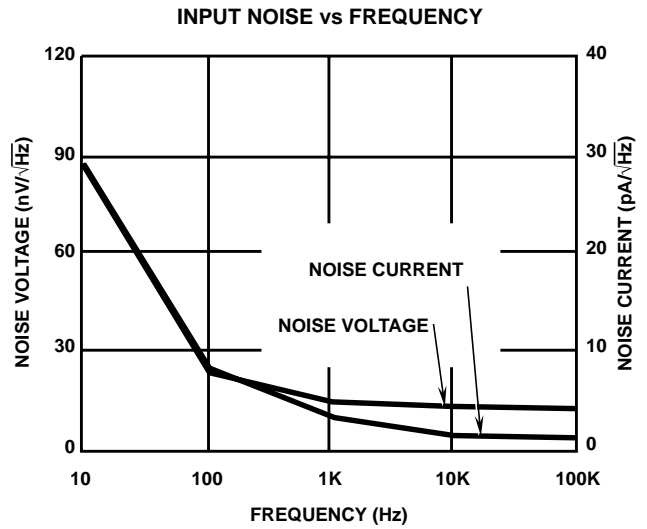
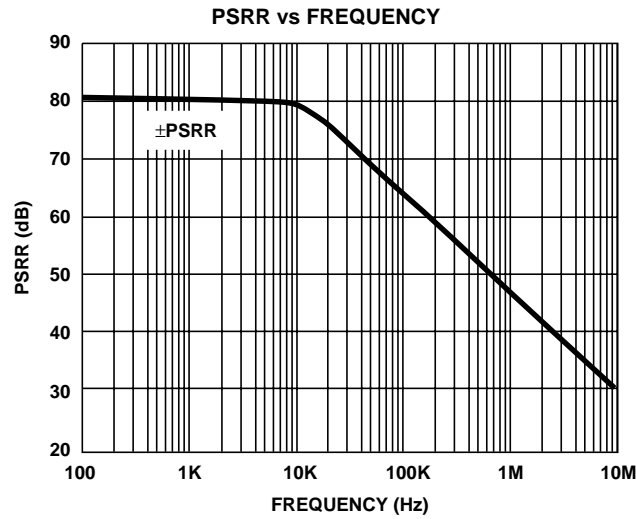
Typical Performance Curves $V_{SUPPLY} = \pm 15V$, $A_V = +1$, $R_L = 1k\Omega$, $C_L \leq 10pF$, $T_A = +25^\circ C$, Unless Otherwise Specified.



DESIGN INFORMATION (Continued)

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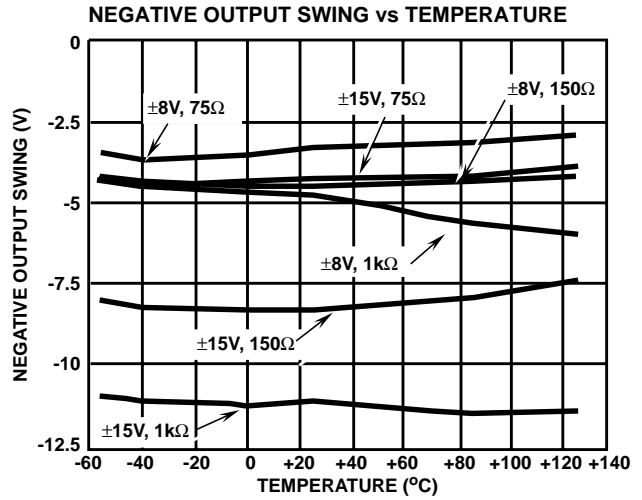
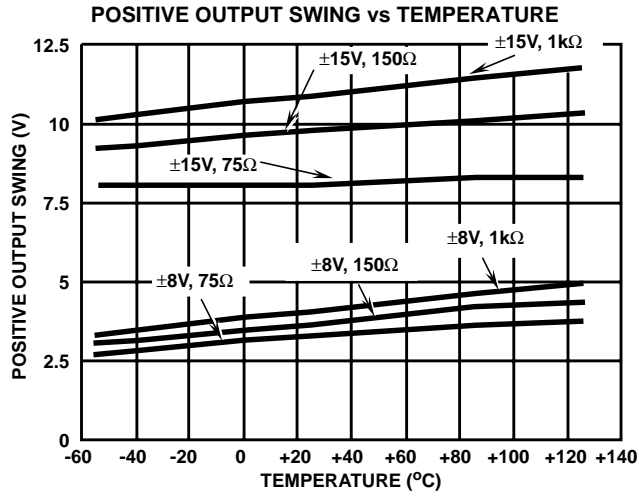
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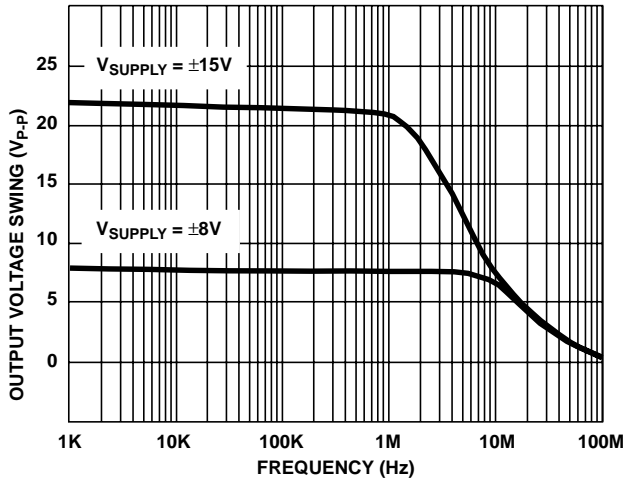
DESIGN INFORMATION (Continued)

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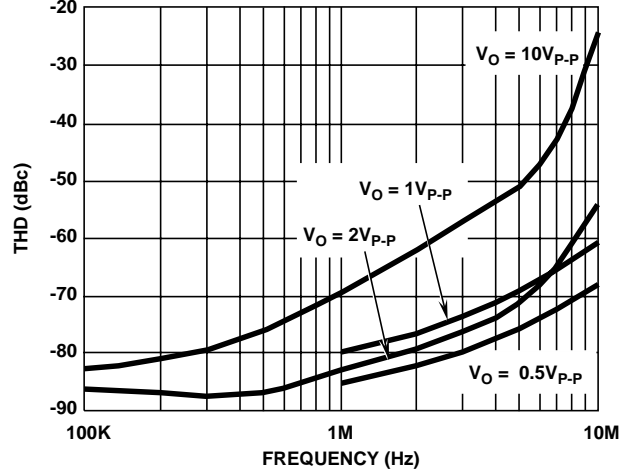
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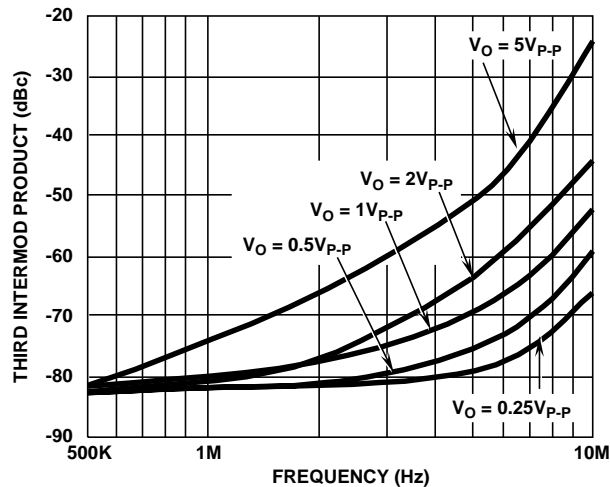
MAXIMUM UNDISTORTED OUTPUT SWING vs FREQUENCY



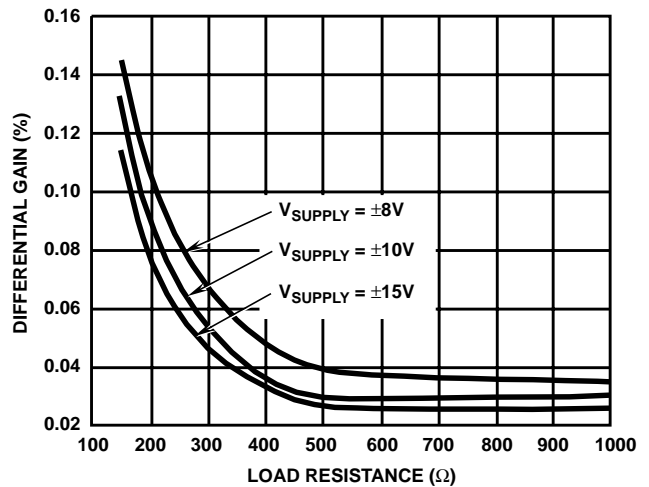
TOTAL HARMONIC DISTORTION vs FREQUENCY



INTERMODULATION DISTORTION vs FREQUENCY (TWO TONE)



DIFFERENTIAL GAIN vs LOAD RESISTANCE

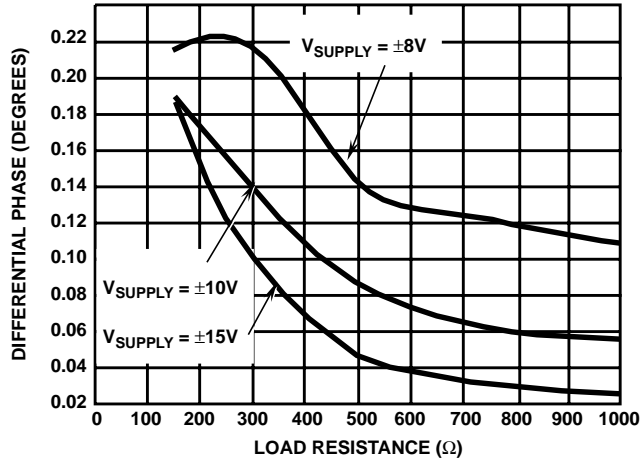


DESIGN INFORMATION (Continued)

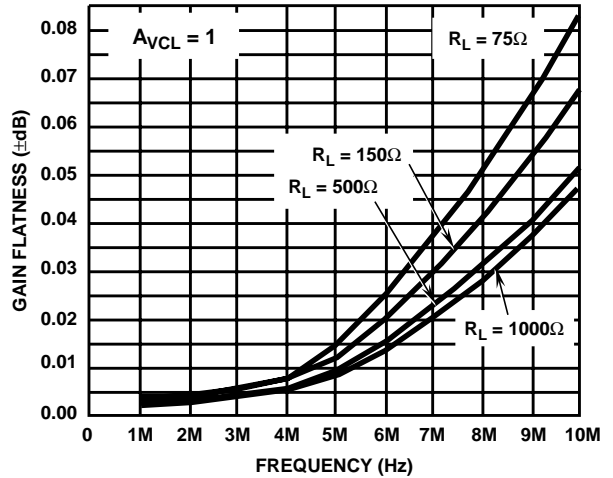
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Typical Performance Curves $V_{SUPPLY} = \pm 15V$, $A_{VCL} = +1$, $R_L = 1k\Omega$, $C_L \leq 10pF$, $T_A = +25^\circ C$, Unless Otherwise Specified.

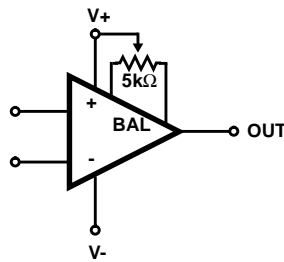
DIFFERENTIAL PHASE vs LOAD RESISTANCE



GAIN FLATNESS vs FREQUENCY



Suggested Offset Voltage Adjustment



HA-2841

TYPICAL PERFORMANCE CHARACTERISTICS

Device Characterized at: $V_{SUPPLY} = \pm 15V$, $R_L = 1k\Omega$, $C_L \leq 10pF$, Unless Otherwise Specified.

| PARAMETERS | CONDITIONS | TEMPERATURE | TYPICAL | UNITS |
|-------------------------------|------------------------------------|-------------|-------------|------------------|
| Input Offset Voltage | $V_{CM} = 0V$ | +25°C | 1 | mV |
| Average Offset Voltage Drift | Versus Temperature | Full | 14 | $\mu V/^\circ C$ |
| Input Bias Current | $V_{CM} = 0V$ | +25°C | 5.0 | μA |
| | | Full | 8.0 | μA |
| Input Offset Current | $V_{CM} = 0V$ | +25°C | 0.5 | μA |
| Differential Input Resistance | | +25°C | 170 | k Ω |
| Input Noise Voltage | $f_O = 10Hz$ to 1MHz | +25°C | 16 | μV_{RMS} |
| Input Noise Voltage Density | $f_O = 1000Hz$ | +25°C | 16 | nV/\sqrt{Hz} |
| Input Noise Current Density | $f_O = 1000Hz$ | +25°C | 2 | pA/\sqrt{Hz} |
| Large Signal Voltage Gain | $V_{OUT} = \pm 10V$ | +25°C | 50 | kV/V |
| | | Full | 30 | kV/V |
| CMRR | $V_{CM} = \pm 2V$ | Full | 95 | dB |
| Gain Bandwidth Product | $f = 10MHz$ | +25°C | 50 | MHz |
| Output Voltage Swing | | Full | ± 10.5 | V |
| Output Current | $V_{OUT} > 10V$ | Full | 30 | mA |
| Output Resistance | Open Loop | +25°C | 8.5 | Ω |
| Full Power Bandwidth | $FPBW = SR/2\pi V_P$, $V_P = 10V$ | +25°C | 4.6 | MHz |
| Slew Rate | $V_{OUT} = \pm 5V$, $A_V = +2$ | +25°C | 290 | V/ μs |
| Rise Time | $V_{OUT} = \pm 100mV$, $A_V = +2$ | +25°C | 3.5 | ns |
| Overshoot | $V_{OUT} = \pm 100mV$, $A_V = +2$ | +25°C | 47 | % |
| Settling Time | 0.1%, 10V Step, $A_V = +2$ | +25°C | 145 | ns |
| PSRR | Delta $V_S = \pm 10V$ to $\pm 20V$ | Full | 80 | dB |
| Supply Current | No Load | Full | 10 | mA |
| Differential Gain | $R_L = 700\Omega$ | +25°C | 0.03 | % |
| Differential Phase | $R_L = 700\Omega$ | +25°C | 0.03 | Degrees |
| Gain Flatnes to 5MHz | $R_L = 75\Omega$ | +25°C | ± 0.015 | dB |
| Gain Flatness to 10MHz | $R_L = 75\Omega$ | +25°C | ± 0.05 | dB |

All Intersil semiconductor products are manufactured, assembled and tested under **ISO9000** quality systems certification.

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